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of Commerce Attorney Docket No. Serial No. Form PTO-1449 U.S. Depart 5308-162 Patent and Trademark Office To Be Assigned Applicants: LIST OF DOCUMENTS CITED BY APPLICANT Robert C. Glass et al. (Use several sheets if necessary) Filing Date: GAU: To Be Assigned **U.S. PATENT DOCUMENTS** Name Class Subclass Examiner Document No. Date Initials 6,177,688 01/23/01 Linthicum et al. 257 77 01/02/01 257 79 2 6,169,294 Biing-Jye et al. 3 6,133,589 10/17/00 Krames et al. 257 103 4 6,121,637 09/19/00 Isokawa et al. 257 99 09/19/00 Morita et al. 257 99 5 6,121,636 257 98 6,097,041 08/01/00 Lin et al. 6 257 98 7 6,091,085 07/18/00 Lester 257 98 04/04/00 Wang et al. 8 6,046,465 9 5,952,681 09/14/99 Chen 257 89 10 5,917,202 06/29/99 Haitz et al. 257 98 11 5,912,477 06/15/99 Negley 257 95 07/14/98 Krames et al. 216 24 12 5,779,924 257 749 13 5,767,581 06/16/98 Nakamura et al. Carter et al. 117 14 5,718,760 02/17/98 84 257 77 06/04/96 Edmond et al. 15 5,523,589 257 05/16/95 76 16 5,416,342 Edmond et al. 17 5,393,993 02/28/95 Edmond et al. 257 77 18 5,247,533 09/21/93 Okazaki et al. 372 45 5,210,051 437 107 19 05/11/93 Carter, Jr. 257 77 20 5,187,547 02/16/93 Niina et al. 5,087,949 02/11/92 Haitz 357 17 21 5,006,908 04/09/91 Matsuoka et al. 357 17 22 10/30/90 437 100 23 4,966,862 Edmond FOREIGN PATENT DOCUMENTS Document Number Date Country Class Subclass 08/09/00 24 GB 2 346 480 A United Kingdom 25 2000-195827 07/14/00 Japan 26 EP 0 961 328 A2 12/01/99 **EPO** 27 10-256604 09/25/98 Japan 28 9-82587 03/28/97 Japan 29 1-225377 09/08/89 Japan 30 56-131977 10/15/81 Japan

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David B. Slater, Jr. et al.

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